

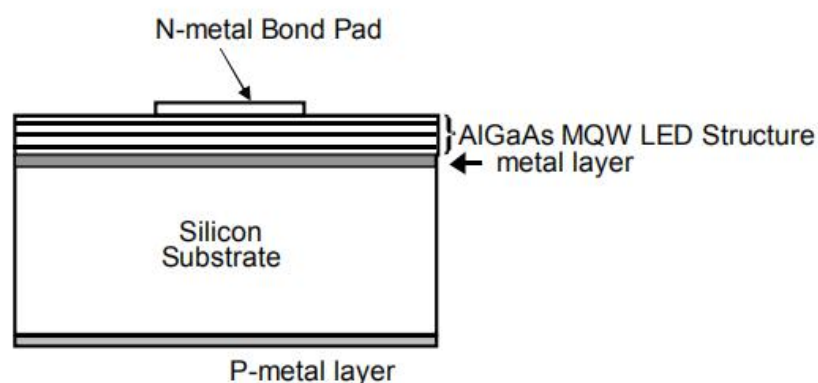
# IN-F26IR-D

## Great Performances:

- Larger Emitting Area
- 100% Tested & Sorted
- Conductive Si-substrate
- Outdoor Applications
- Rough Surface

## Descriptions:

F26IR is a Infra-red LED chip made from MOCVD process and bonded with Silicon. It is fabricated by the proprietary metal Bonding mechanism, F26IR is featured by homogeneous and high light output at top side with superior beam pattern. Excellent performance under sunlight and reliable life-long stability make F26IR ideal for IrDA, Encoder, data communication applications.



## Chip Dimension

1. Chip size:  $620 \pm 25\mu\text{m} \times 620 \pm 25\mu\text{m}$
2. Chip thickness:  $180 \pm 15\mu\text{m}$
3. N-bonding pad: Au pad  $\phi 104 \pm 15\mu\text{m}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	$V_{F1}$	1.3	1.5	1.8	V	$I_F=150\text{ mA}$
Threshold Voltage	$V_{F3}$	1.0	-	1.3	V	$I_F=10\ \mu\text{A}$
Reverse Current	$I_R$	-	-	10.0	$\mu\text{A}$	$V_R=5\text{ V}$
Peak Wavelength	$\lambda_p$	800	-	900	nm	$I_F=150\text{ mA}$
Spectral Line Half Width	$\Delta\lambda$	-	30	-	nm	$I_F=150\text{ mA}$
Radiation Power	$P_o$	25	-	-	mW	$I_F=150\text{ mA}$

\*  $P_o$  is measured on chip form with HPO's tester.